

N-Channel Enhancement Mode MOSFET

1. Product Information

Features

SGT technology
Excellent $R_{DS(ON)}$
Low gate charge

Pin Description

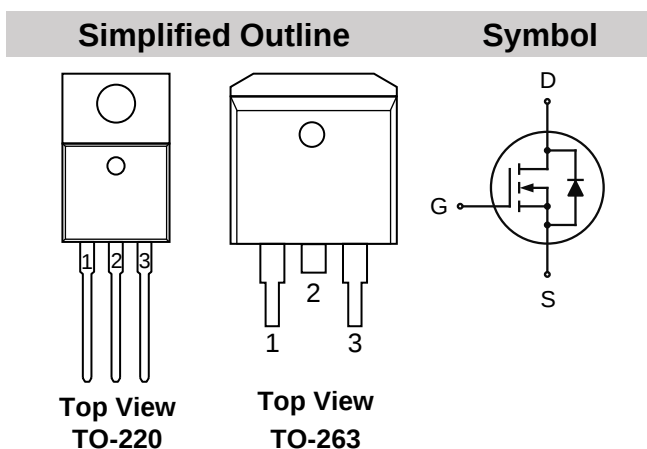
Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

Applications

BMS
UPS
Power management Switches

Quick reference

$V_{DS} \geq 120V$
 $I_D \leq 200A$
 $R_{DS(ON)} \leq 4.2 m\Omega @ V_{GS}=10V$ (Type: 3.7m Ω)



Package Marking and Ordering Information

Product Name	Package	Marking	Reel Size	Tape width	Quantity
KJ200N12C	TO-220	KJ200N12C	-	-	1000
KJ200N12D	TO-263	KJ200N12D	-	-	800

2. Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	120	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_{D@T_C=25^\circ C}$	Continuous Drain Current, $V_{GS} @ 10V$	200	A
$I_{D@T_C=100^\circ C}$	Continuous Drain Current, $V_{GS} @ 10V$	150	A
I_{DM}	Pulsed Drain Current	600	A
E_{AS}	Single Pulse Avalanche Energy	530	mJ
I_{AS}	Avalanche Current	45	A
$P_{D@T_C=25^\circ C}$	Total Power Dissipation ⁴	240	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	0.75	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case	62	$^\circ C/W$

3. Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Type	Max.	Unit
VDSS	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	120	135	-	V
IGSS	Gate-body Leakage current	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
IDSS	Zero Gate Voltage Drain Current T _J =25°C	V _{DS} =120V, V _{GS} = 0V	-	-	1	μA
IDSS	Zero Gate Voltage Drain Current T _J =100°C		-	-	100	
VGS(th)	Gate-Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	2.9	4.0	V
RDS(on)	Drain-Source on-Resistance ²	V _{GS} = 10V, I _D = 20A	-	3.7	4.2	mΩ
RDS(on)	Drain-Source on-Resistance ²	V _{GS} = 6V, I _D = 20A	-	4.3	5.8	mΩ
Ciss	Input Capacitance	V _{GS} = 0V, V _{DS} = 60V, f = 250kHz	-	5240	-	pF
Coss	Output Capacitance		-	739	-	
Crss	Reverse Transfer Capacitance		-	12	-	
R _g	Gate Resistance	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz	-	1.7	-	Ω
Q _g	Total Gate Charge	V _{DD} =60V, I _D = 45A, V _{GS} =0 to 10V	-	19	-	nC
Q _{gs}	Gate-Source Charge		-	11	-	
Q _{gd}	Gate-Drain Charge		-	75	-	
td(on)	Turn-on Delay Time	V _{DD} = 60V, V _{GS} = 10V, I _D =45A, R _G =10Ω	-	59	-	ns
t _r	Rise Time		-	41	-	
td(off)	Turn-off Delay Time		-	96	-	
t _f	Fall Time		-	33	-	
VSD	Diode Forward Voltage ²	I _F = 20A, V _{GS} = 0V	-	0.8	1.2	V
IS	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	-	-	200	A
trr	Body Diode Reverse Recovery Time	VR=60V I _F =35A, dI/dt=100A/μs	-	70	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge		-	200	-	nC

Notes:

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3、The EAS data shows Max. rating . The test condition is V_{DD}=50V, V_{GS}=10V, L=0.5mH, I_{AS}=45A
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

4. Typical Characteristics

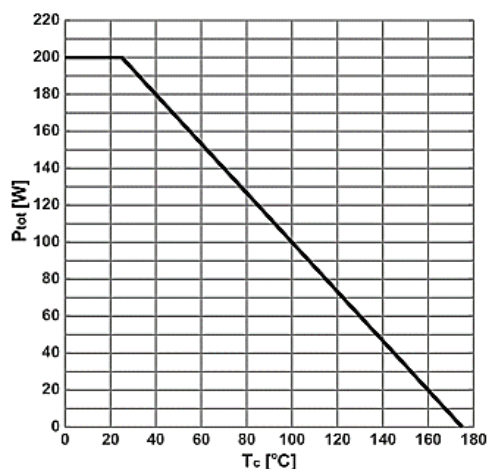


Figure 1. Power dissipation

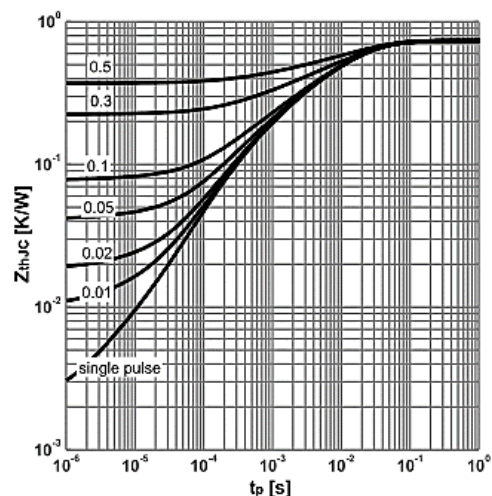


Figure 2. Max. transient thermal impedance

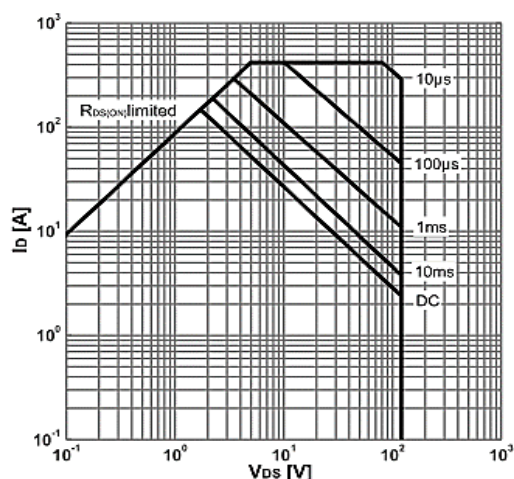


Figure 3. Safe operating area

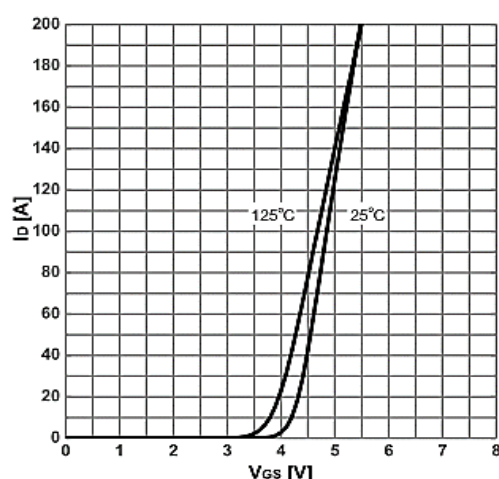


Figure 4. Type. transfer characteristics

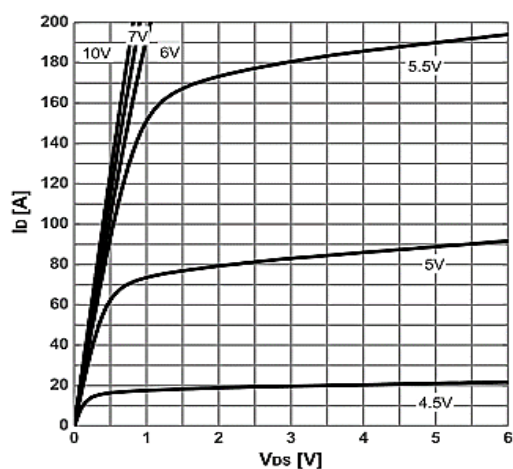


Figure 5. Typ. output characteristics(Tj 25°C)

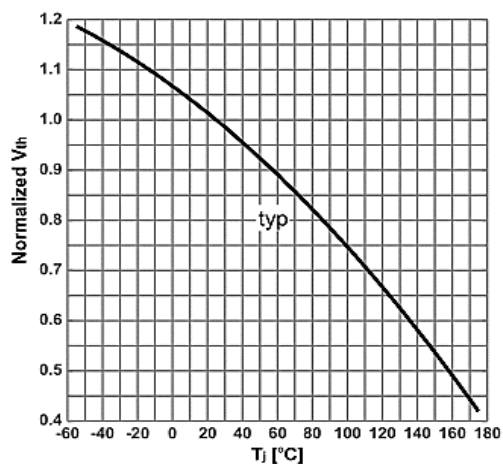


Figure 6. Typ. output characteristics(Tj 125°C)

4. Typical Characteristics (cont.)

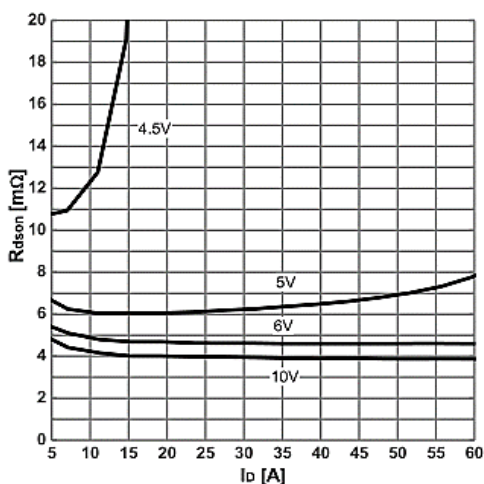


Figure 7. On-state resistance vs. Drain current

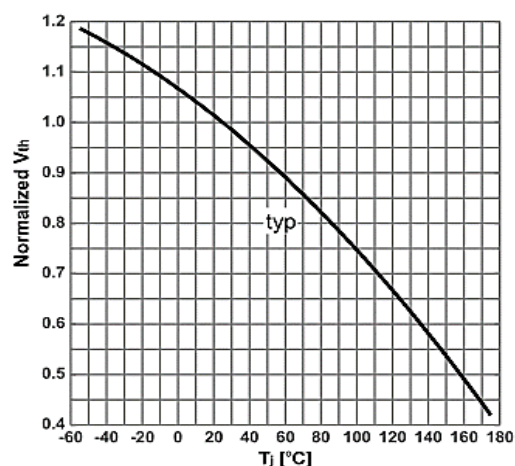


Figure 6. Gate threshold voltage vs. Junction Temperature

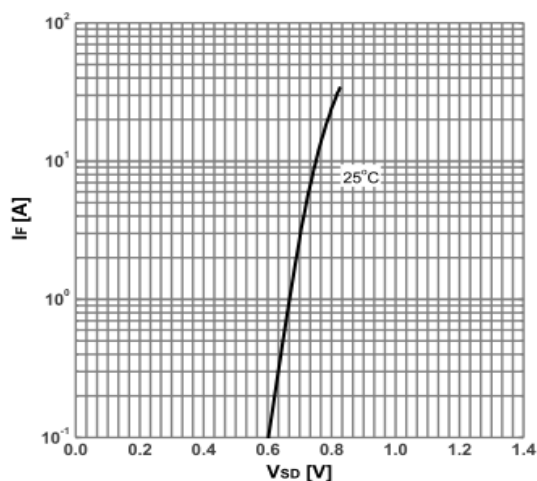


Figure 9. Forward characteristics of reverse diode

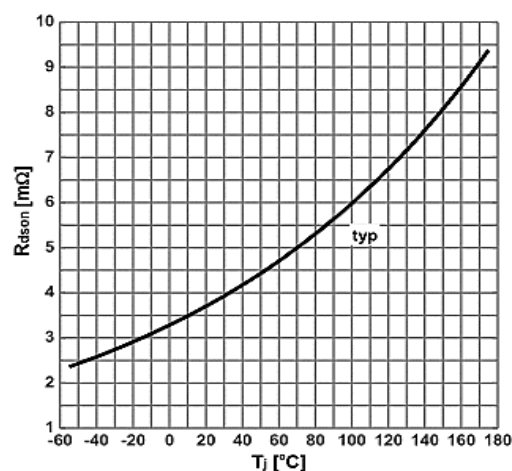


Figure 8. On-state resistance vs. Junction temperature

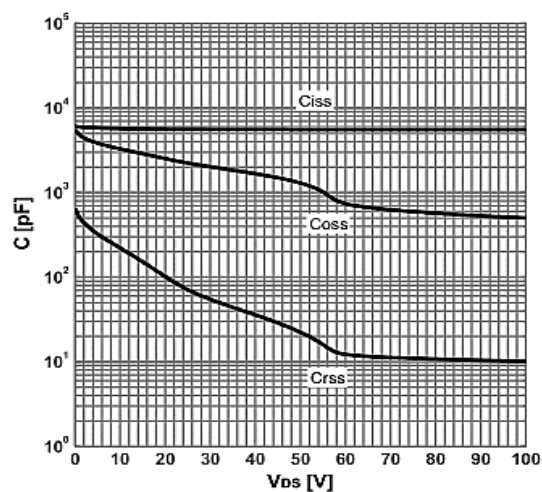


Figure9 Typ. capacitances

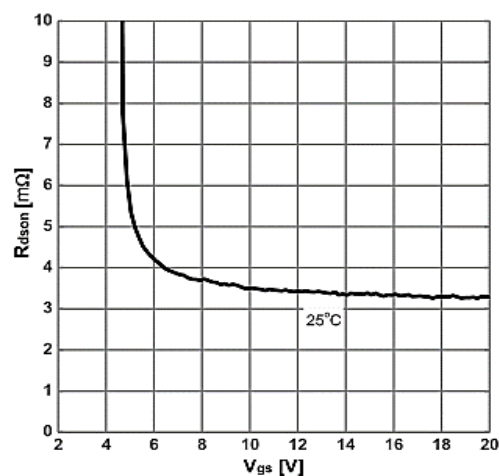


Figure11. On-state resistance vs. Vgs characteristics

4. Typical Characteristics (cont.)

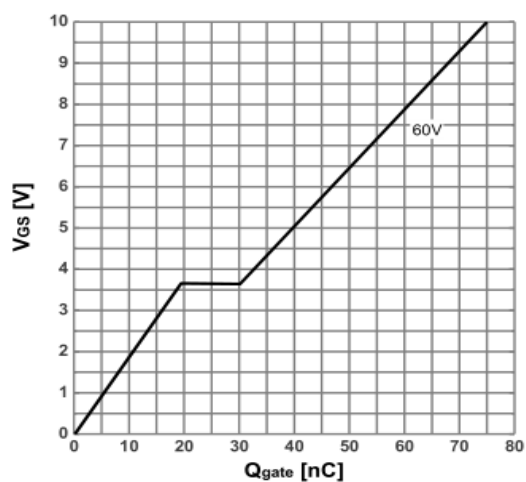
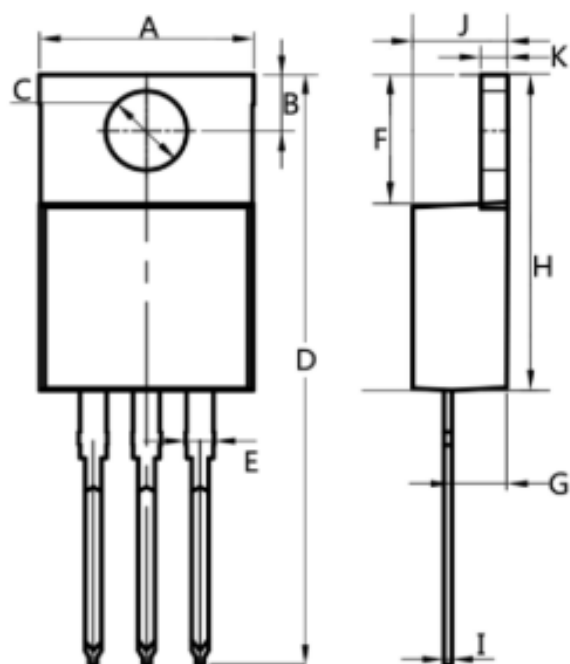


Figure 13: Typ. gate charge

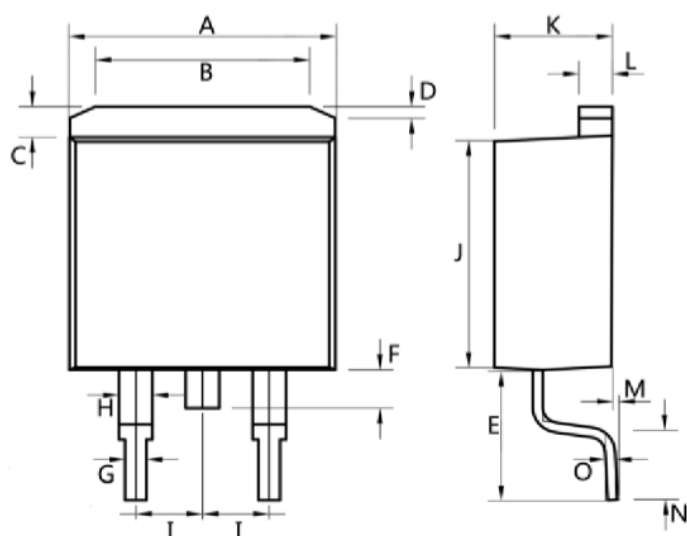
5. Package Mechanical Data

TO-220 Package



Dim.	Min.	Max.
A	10.0	10.4
B	2.5	3.0
C	3.5	4.0
D	28.0	30.0
E	1.1	1.5
F	6.2	6.6
G	2.9	3.3
H	15.0	16.0
I	0.35	0.45
J	4.3	4.7
K	1.2	1.4
All Dimensions in millimeter		

TO-263 Package



Dim.	Min.	Max.
A	10.0	10.5
B	7.25	7.75
C	1.3	1.5
D	0.55	0.75
E	5.0	6.0
F	1.4	1.6
G	0.75	0.95
H	1.15	1.35
I	Typ 2.54	
J	8.4	8.6
K	4.4	4.6
L	1.25	1.45
M	0.02	0.1
N	2.4	2.8
O	0.35	0.45
All Dimensions in millimeter		